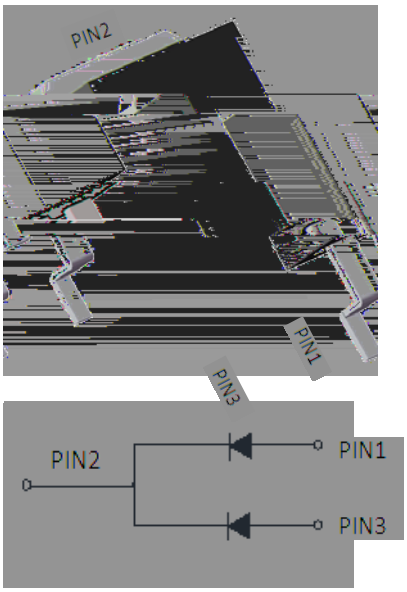
MBRB20100CT THRU MBRB20200CT

RoHS COMPLIANT

Schottky Diodes



Features

- High frequency operation
- High surge capacity
- Guard ring for transient protection
- Meets MSL level 1, per J-STD-020, LF maximum peak of

- **Polarity** As marked

Maximum Ratings (Tc = 25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRB20100CT	MBRB20150CT	MBRB20200CT
Device marking code			MBRB20100CT	MBRB20150CT	MBRB20200CT
Repetitive peak reverse voltage	V_{RRM}	V			
Average rectified forward current (Rated V_R)	$I_{F(AV)}$	A			
Peak repeating forward current (Rated V_R, square wave, 20kHz) at T_C = 125°C	I_{FRM}	A			
Non-repetitive peak surge current (Surge applied at rated load conditions, halfwave, single phase, 60Hz)	I_{FSM}	A			
Voltage rate of change (Rated V_R)	dv/dt	V/μs			
Operating junction temperature	T_J	°C			
Storage temperature	T_{STG}	°C			

Electrical Characteristics (Tc = 25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRB20100CT	MBRB20150CT	MBRB20200CT
Maximum instantaneous forward voltage drop per leg	V_F	V	I_F = 10A			
Maximum DC reverse current at rated DC blocking voltage per leg	I_R	μA	T_C = 25°C			
		mA	T_C = 125°C			

Note: Pulse test: 300μs pulse width, 1% duty cycle

Note: Pulse test: pulse width 5ms, duty cycle 2%

v**Thermal Characteristics** Ä 7D 8QOHVV RWKHUÅLVH VSHFLILHG

PARAMETER	SYMBOL	UNIT	MBRB20100CT	

Disclaimer

7KH LQIRUPDWLRQ \SURGHRVFXPHQWDWLRQ LQ WKLV<UDQH[HRQXFKDQJH(OHFWURQLFV /WG UHV
ULJKW WR PDNH FKDQJHV WR WKHVH SHFLILFDWLRQV GLVFRQWLQXDQFHV RU WR DQ\ GLVFORVXUHV GDWH
RU RWKHUZLVH

7KH SURGXFWQDLVVGHVLJQHGL WR EHXVHGLQRQLHQGXVWULDOLQHKLFRUHGXQGDQWQW RU GHYLFHVWKDQG Q
HTXLSPHQW RU GHYLFHV ZKLFK UHTXLWKHKPDKOIXZQVWKLZRQXBHQGGDEQHWWKXQDQDOIH
PHGLFDO LQVWUXPHQWVRUSURVWHQHVLV DQ GHYLFHV <DQJML HLVRU EHQKBQH RQ VXPHLVLQ\RUHVSRELQLEWHVRO WDLQQJGDRPJXWXFK LP
RI VDOH

7KLV SXEOLFDWLRQSVXSHUVHGHVLQURU\PDXSLQGHVLQURXGG LWLRQDO LQWRUPDWLR
KWWZZZ \DQJML HRFRP QVXOW \RXU QHDUHVW <DQJMLHWHFKQRORJLHV RIILFH IRU IXUW